

|                            |           |      |        |
|----------------------------|-----------|------|--------|
| SPEC SHEET (FOR REFERENCE) | SHEET No. | Rev. | Page.  |
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**TYPE:6PT2006N3T \* \***

|                        |               |
|------------------------|---------------|
| CHIP SIZE              | 0.23 * 0.23mm |
| WAFER SIZE             | 6inch         |
| POSSIBLE DIE PER WAFER | 290,000pcs    |

Maximum Ratings (Ta=25°C)

| Characteristics      | Symbol | Ratings | Unit |
|----------------------|--------|---------|------|
| Drain-source voltage | VDSS   | 60      | V    |
| Gate-source voltage  | VGSS   | ±20     | V    |

WAFER PROBING SPEC (Ta=25°C)

| TEST NO. | MODE  | LIMIT |     |      | UNIT | CONDITION         |
|----------|-------|-------|-----|------|------|-------------------|
|          |       | MIN   | Typ | MAX  |      |                   |
| 1        | IGSS  |       |     | ±5   | uA   | VGS=±20V VDS=0V   |
| 2        | IDSS  |       |     | 500  | nA   | VDS=60V VGS=0V    |
| 3        | BVDSS | 63    |     |      | V    | ID=1mA            |
| 4        | VTH   | 1     |     | 2.4  | V    | VDS=10V IDS=100uA |
| 5        | Ron 1 |       | 5.5 | 7.5  | Ω    | ID=50mA VGS=10V   |
| 6        | Ron 2 |       | 8   | 10.5 | Ω    | ID=30mA VGS=4.0V  |
| 7        | VSD   |       |     | 1.2  | V    | IS=100mA          |

※ Built-in ZD between Gate and Source

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NOTE: